Title (en)

PROCESS FOR DEPOSITING A LARGE-SURFACE LAYER THROUGH A MASK AND OPTIONAL CLOSURE OF SAID MASK

Title (de)

VERFAHREN ZUM ABSCHEIDEN EINER GANZFLÄCHIGEN SCHICHT DURCH EINE MASKE UND OPTIONALEM VERSCHLIESSEN DIESER MASKE

Title (fr)

PROCEDE DE DEPOT D'UNE COUCHE A LARGE SURFACE A TRAVERS UN MASQUE ET OBTURATION FACULTATIVE DUDIT MASQUE

Publication

EP 0697110 A1 19960221 (DE)

Application

EP 94914319 A 19940505

Priority

- DE 9400505 W 19940505
- DE 4314888 A 19930505

Abstract (en)

[origin: DE4314888C1] By deposition from different directions through a mask, a layer can be applied under this mask over the total surface last. The mask is in this case separated in the coating region from the background by a cavity and is firmly attached thereto outside the coating region. This method is particularly advantageous for the SGFET (suspended gate field effect transistor) used as a gas sensor. In this case, the mask also forms the gate and the sensitive layer is not exposed to any other process after the deposition. The mask can afterwards be left open or be closed by depositing a sufficient quantity for the openings in the mask to be laterally covered over, or by depositing an additional layer under a shallow angle. This method is also suitable for the production of micromechanical diaphragms.

IPC 1-7

G01N 27/414; G01N 33/00; G01L 9/00; G01P 15/08

IPC 8 full level

G01L 1/18 (2006.01); **C23C 14/04** (2006.01); **G01L 9/00** (2006.01); **G01N 27/00** (2006.01); **G01N 27/414** (2006.01); **G01N 29/00** (2006.01); **G01N 33/00** (2006.01); **G01P 15/08** (2006.01)

CPC (source: EP US)

C23C 14/042 (2013.01 - EP US); **G01N 27/4143** (2013.01 - EP US)

Citation (search report)

See references of WO 9425863A2

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

DE 4314888 C1 19940818; DE 59406507 D1 19980827; EP 0697110 A1 19960221; EP 0697110 B1 19980722; EP 0811771 A2 19971210; EP 0811771 A3 20040211; JP 3577080 B2 20041013; JP H08511092 A 19961119; US 5786235 A 19980728; WO 9425863 A2 19941110; WO 9425863 A3 19950112

DOCDB simple family (application)

DE 4314888 A 19930505; DE 59406507 T 19940505; DE 9400505 W 19940505; EP 94914319 A 19940505; EP 97114672 A 19940505; JP 52375694 A 19940505; US 53791595 A 19951031